

P-Channel Switch

J176, MMBFJ176

Description

This device is designed for low-level analog switching sample-and-hold circuits and chopper-stabilized amplifiers. Sourced from process 88.

ABSOLUTE MAXIMUM RATINGS (Note 1, Note 2)

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{DG}	Drain-Gate Voltage	-30	V
V_{GS}	Gate-Source Voltage	30	V
I_{GF}	Forward Gate Current	50	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

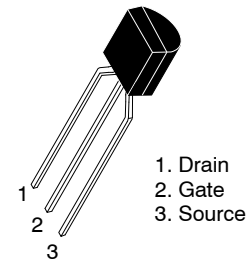
- These ratings are based on a maximum junction temperature of 150°C .
- These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty cycle operations.

THERMAL CHARACTERISTICS

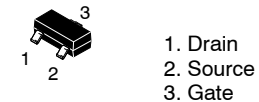
Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Max.		Unit
		J176 (Note 3)	MMBFJ176, (Note 3)	
P_D	Total Device Dissipation	350	225	mW
	Derate Above 25°C	2.8	1.8	mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	-	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	$^\circ\text{C}/\text{W}$

- PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.



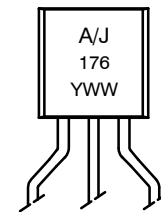
TO-92 3 LF
CASE 135AR



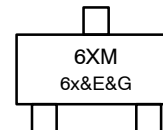
SOT-23
(TO-236)
CASE 318

Source & Drain are interchangeable.

MARKING DIAGRAMS



A = Assembly Site
J176 = Specific Device Code
Y = Year of Production (Last Number)
WW = Work Week Number



6X = Specific Device Code
M = Assembly Operation Month

ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

ELECTRICAL CHARACTERISTICS Values are at $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit	
OFF CHARACTERISTICS						
V _{(BR)GSS}	Gate-Source Breakdown Voltage	I _G = 1.0 μA, V _{DS} = 0	30	–	V	
I _{GSS}	Gate Reverse Current	V _{GS} = 20 V, V _{DS} = 0	–	1.0	nA	
V _{GS(off)}	Gate-Source Cut-Off Voltage	V _{DS} = –15 V, I _D = –10 nA	J176 / MMBFJ176	1.0	4.0	V

ON CHARACTERISTICS

I_{DSS}	Zero-Gate Voltage Drain Current (Note 4)	$V_{DS} = -15\text{ V}$, $I_{GS} = 0$	J176 / MMBFJ176	-2.0	-25.0	mA
$r_{DS(on)}$	Drain-Source On Resistance	$V_{DS} \leq 0.1\text{ V}$, $V_{GS} = 0$	J176 / MMBFJ176	–	250	Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2.0\%$.

TYPICAL CHARACTERISTICS

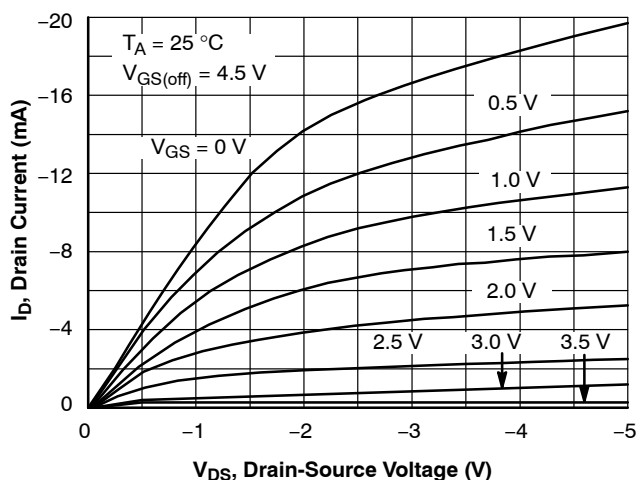


Figure 1. Common Drain-Source

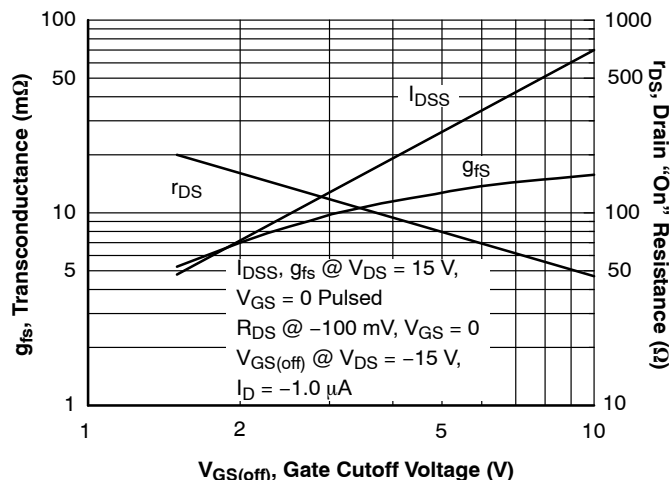


Figure 2. Parameter Interactions

TYPICAL CHARACTERISTICS (continued)

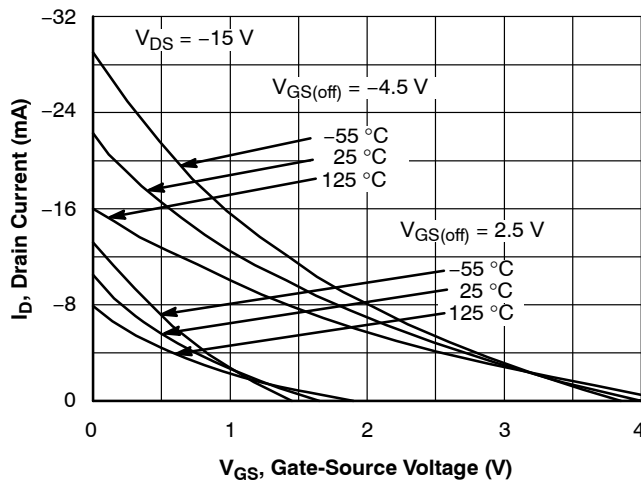


Figure 3. Transfer Characteristics

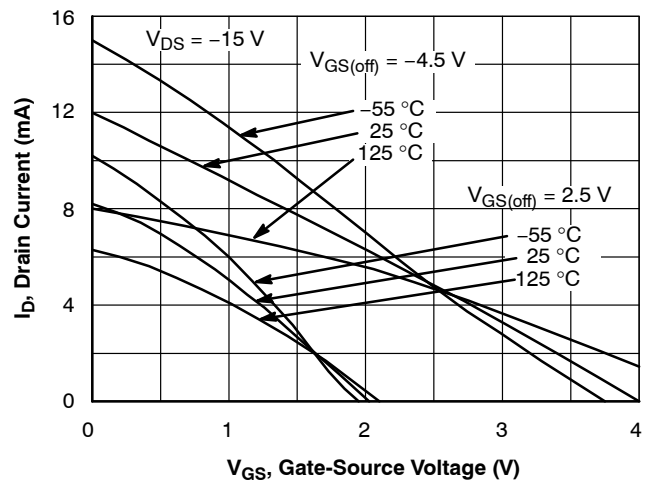


Figure 4. Transfer Characteristics

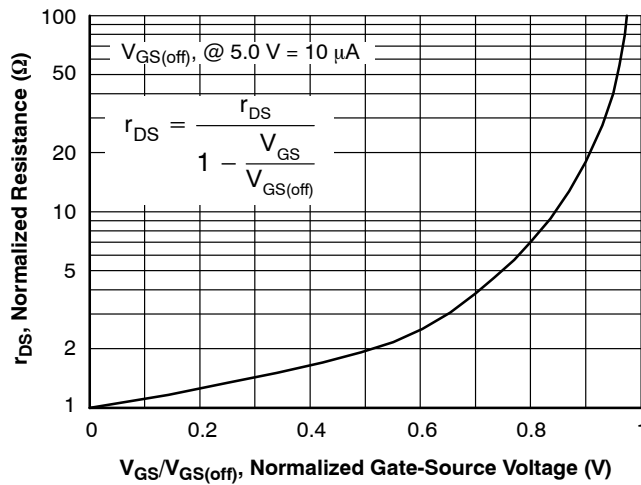


Figure 5. Normalized Drain Resistance vs. Bias Voltage

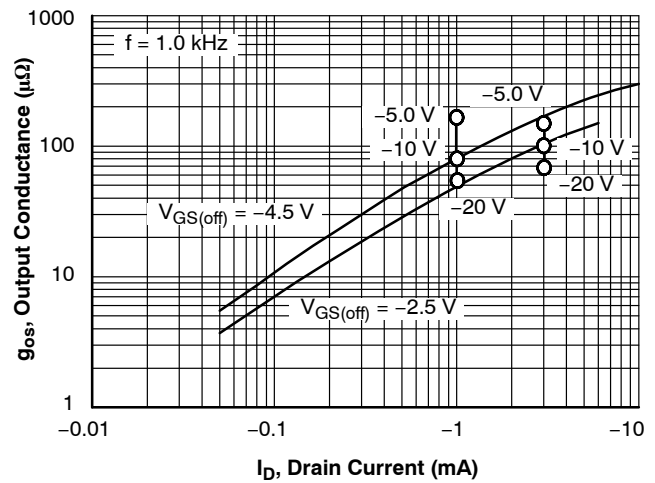


Figure 6. Output Conductance vs. Drain Current

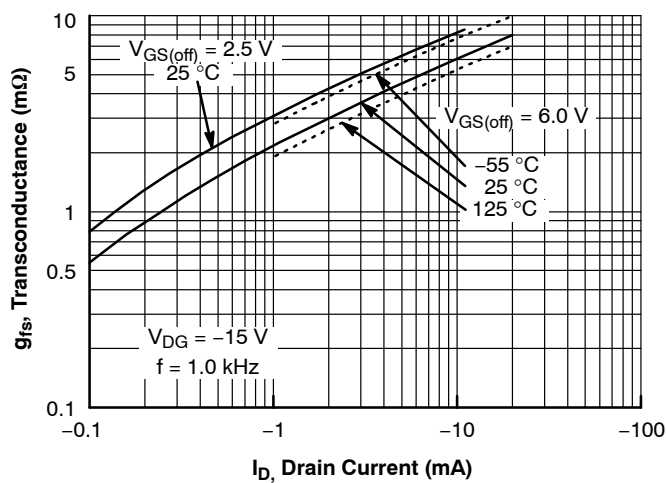


Figure 7. Transconductance vs. Drain Current

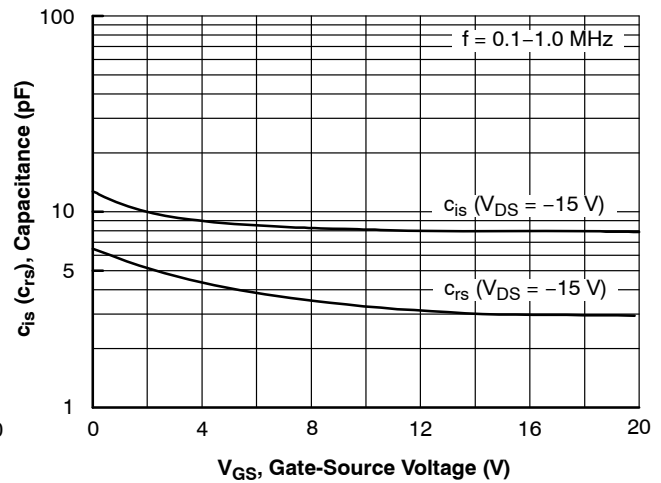


Figure 8. Capacitance vs. Voltage

TYPICAL CHARACTERISTICS (continued)

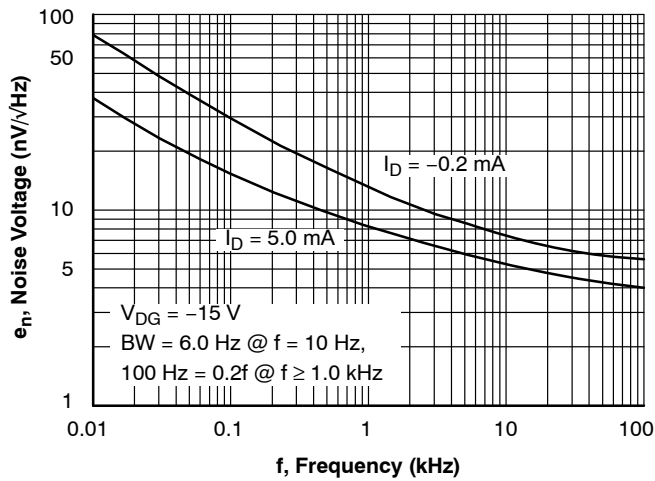


Figure 9. Noise Voltage vs. Frequency

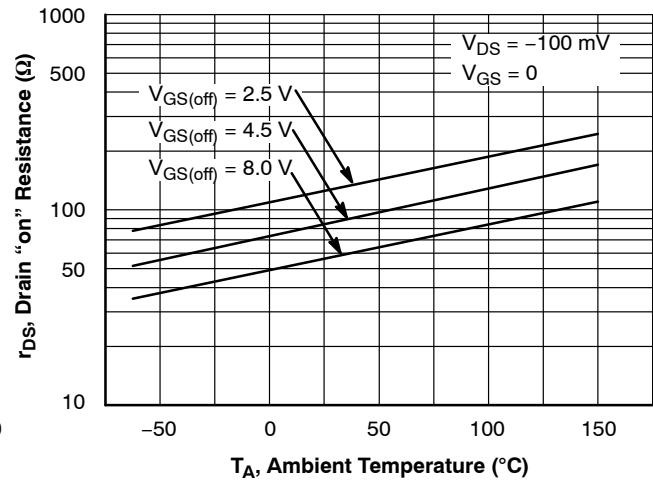


Figure 10. Channel Resistance vs. Temperature

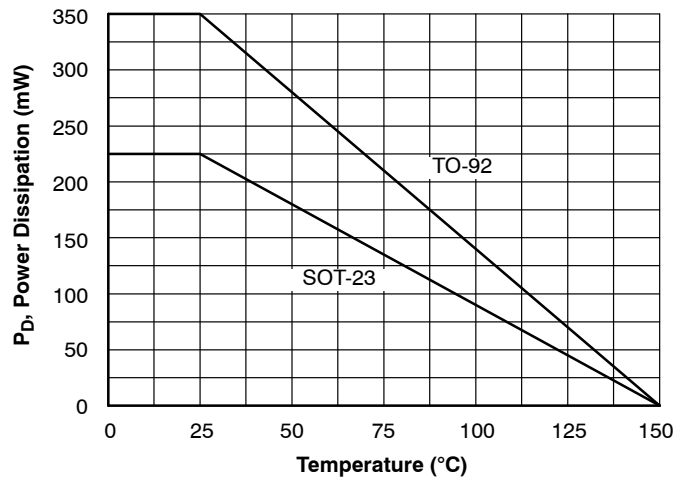


Figure 11. Power Dissipation vs. Ambient Temperature

ORDERING INFORMATION

Part Number	Marking	Package	Packing Method [†]	Min Order Qty / Immediate Pack Qty
J176-D74Z	J176	TO-92 3 LF	Fan-Fold	2000
MMBFJ176	6X	SOT-23 (TO-236)	Tape and Reel	3000

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

REVISION HISTORY

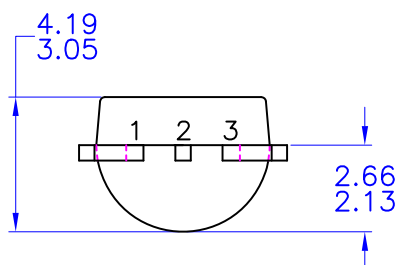
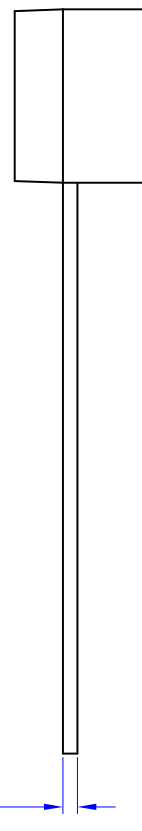
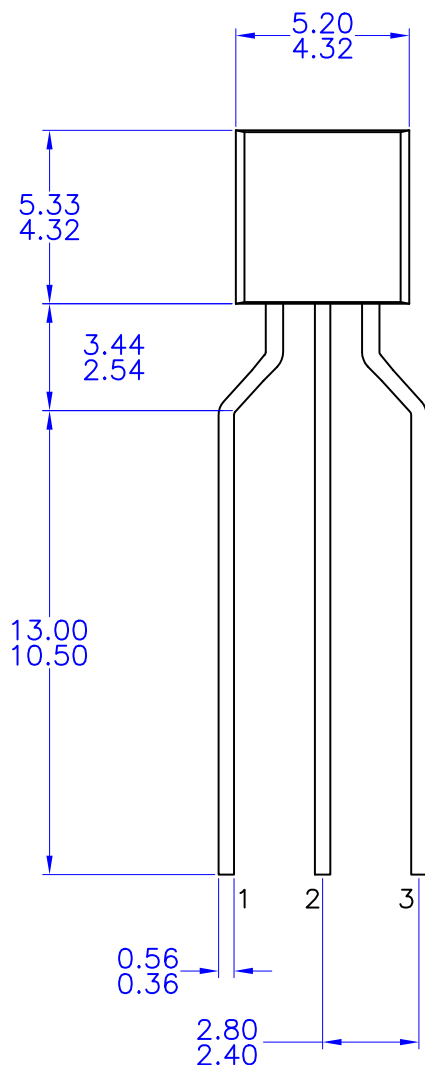
Revision	Description of Changes	Date
3	Converted the Document to onsemi format.	1/26/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.



TO-92 3 4.83x4.76 LEADFORMED
CASE 135AR
ISSUE O

DATE 30 SEP 2016

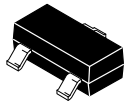


NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994

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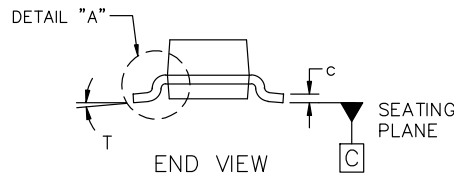
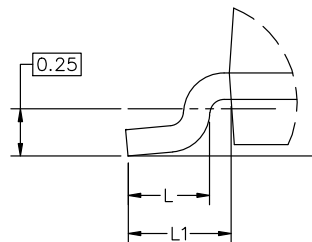
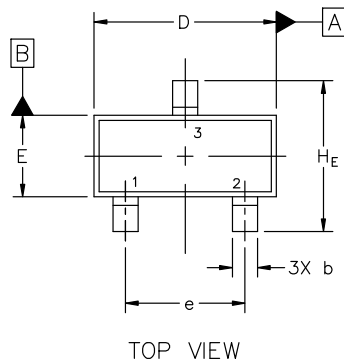
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SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
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ISSUE AU

DATE 14 AUG 2024



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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